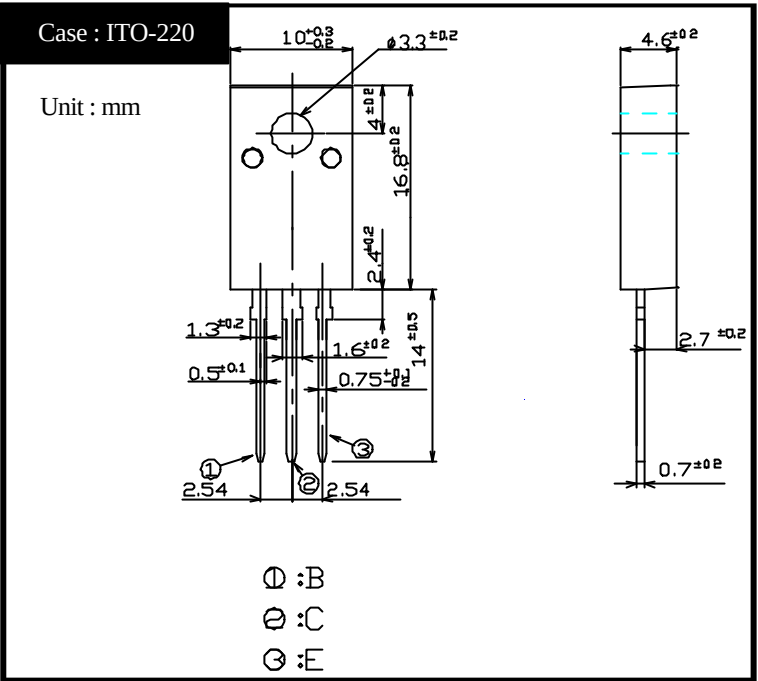


2SC4664
(TP8V20FS)

8A NPN

OUTLINE DIMENSIONS



RATINGS

●Absolute Maximum Ratings

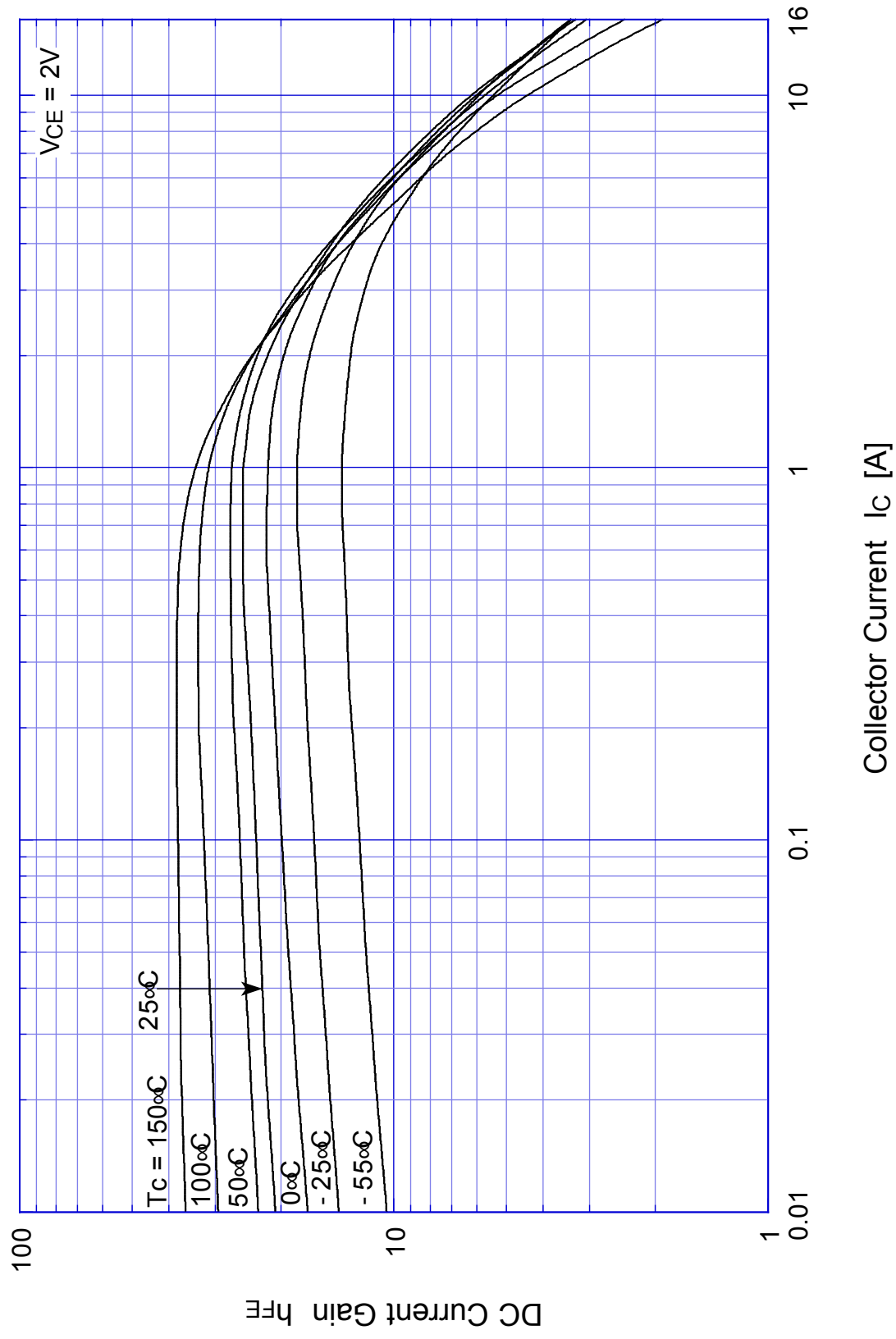
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-55~150	°C
Junction Temperature	T _j		150	°C
Collector to Base Voltage	V _{CBO}		250	V
Collector to Emitter Voltage	V _{CEO}		200	V
Emitter to Base Voltage	V _{EBO}		7	V
Collector Current DC	I _C		8	A
Collector Current Peak	I _{CP}		16	
Base Current DC	I _B		3	A
Base Current Peak	I _{BP}		6	
Total Transistor Dissipation	P _T	T _c = 25°C	30	W
Dielectric Strength	V _{dis}	Terminals to case, AC 1 minute	2	kV
Mounting Torque	TOR	(Recommended torque : 0.3N·m)	0.5	N·m

●Electrical Characteristics (T_c=25°C)

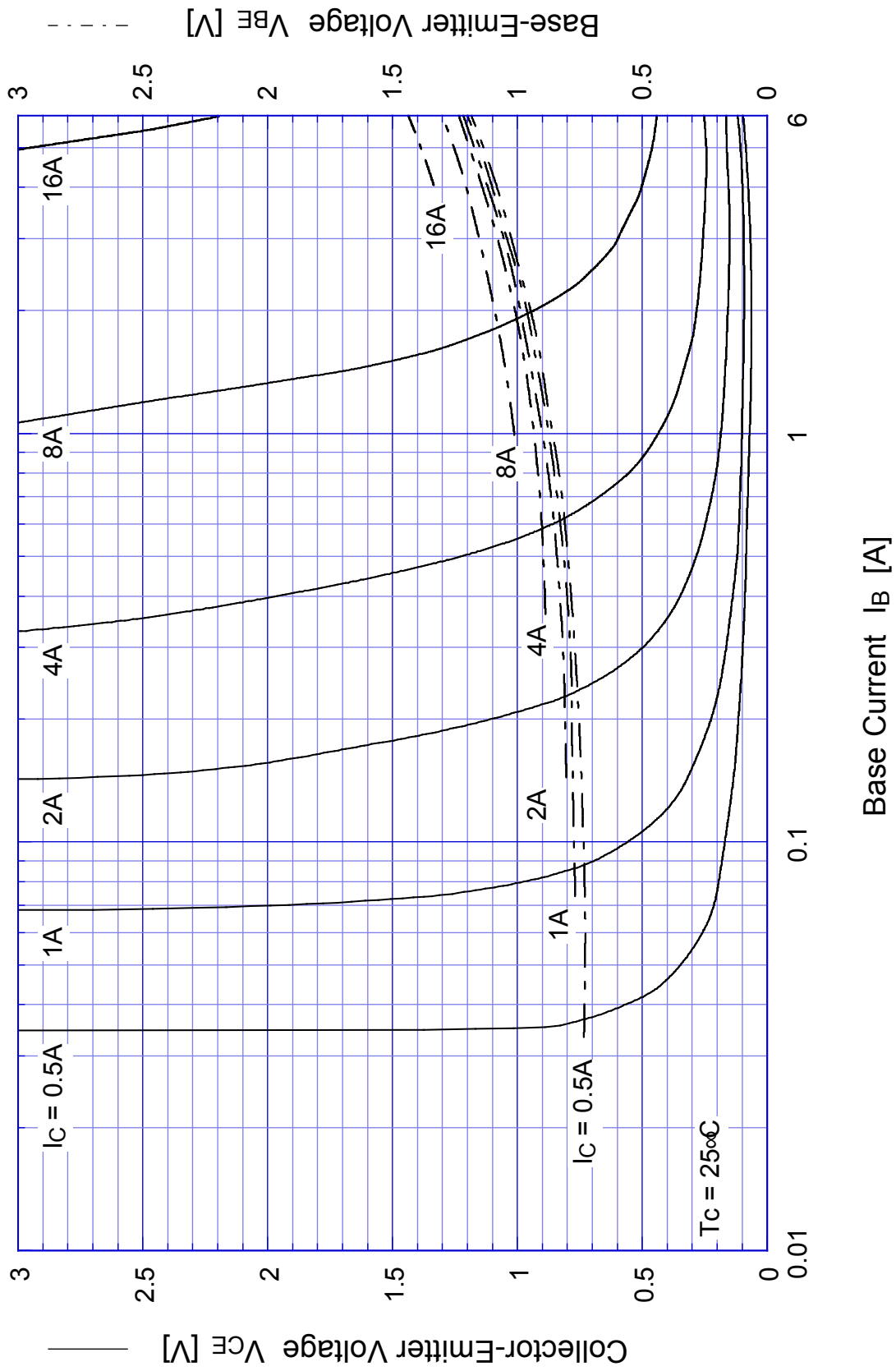
Item	Symbol	Conditions	Ratings	Unit
Collector to Emitter Sustaining Voltage	V _{CEO(sus)}	I _C = 0.1A	Min 200	V
Collector Cutoff Current	I _{CBO}	At rated Voltage	Max 0.1	mA
	I _{CEO}		Max 0.1	
Emitter Cutoff Current	I _{EBO}	At rated Voltage	Max 0.1	mA
DC Current Gain	h _{FE}	V _{CE} = 2V, I _C = 4A	10~25 ^{*1}	
	h _{FEL}	V _{CE} = 2V, I _C = 1mA	Min 10	
Collector to Emitter Saturation Voltage	V _{CE(sat)}	I _C = 4A	Max 1.0	V
Base to Emitter Saturation Voltage	V _{BE(sat)}	I _B = 0.8A	Max 1.5	V
Thermal Resistance	θ _{jc}	Junction to case	Max 4.17	°C/W
Transition Frequency	f _T	V _{CE} = 10V, I _C = 0.8A	TYP 13	MHz
Turn on Time	ton	I _C = 4A	Max 0.3	μs
Storage Time	ts	I _{B1} = 0.8A, I _{B2} = 1.6A	Max 1.0	
Fall Time	tf	R _L = 37.5Ω, V _{BB2} = 4V	Max 0.1	

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$h_{FE} - I_C$

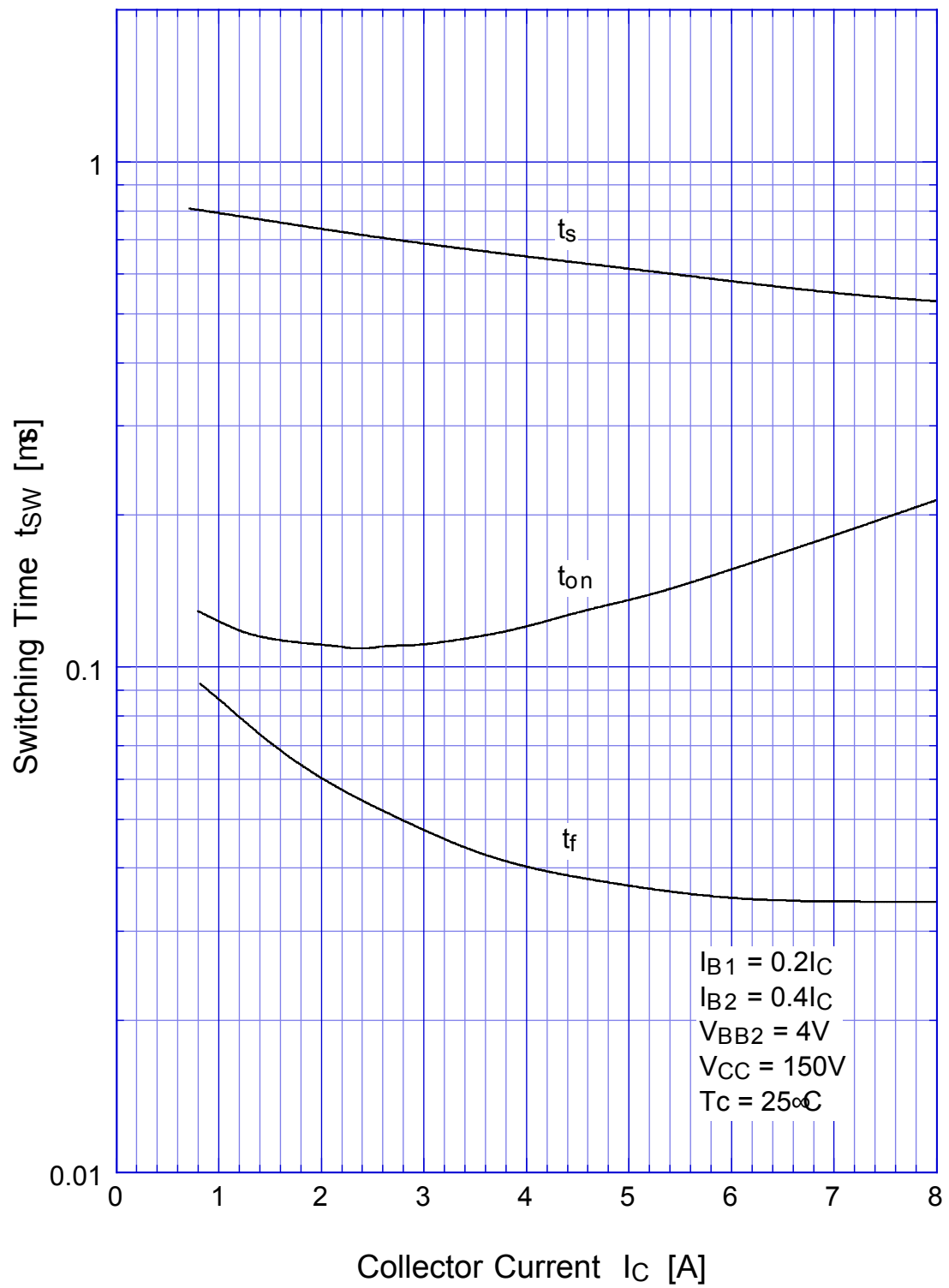


2SC4664 Saturation Voltage



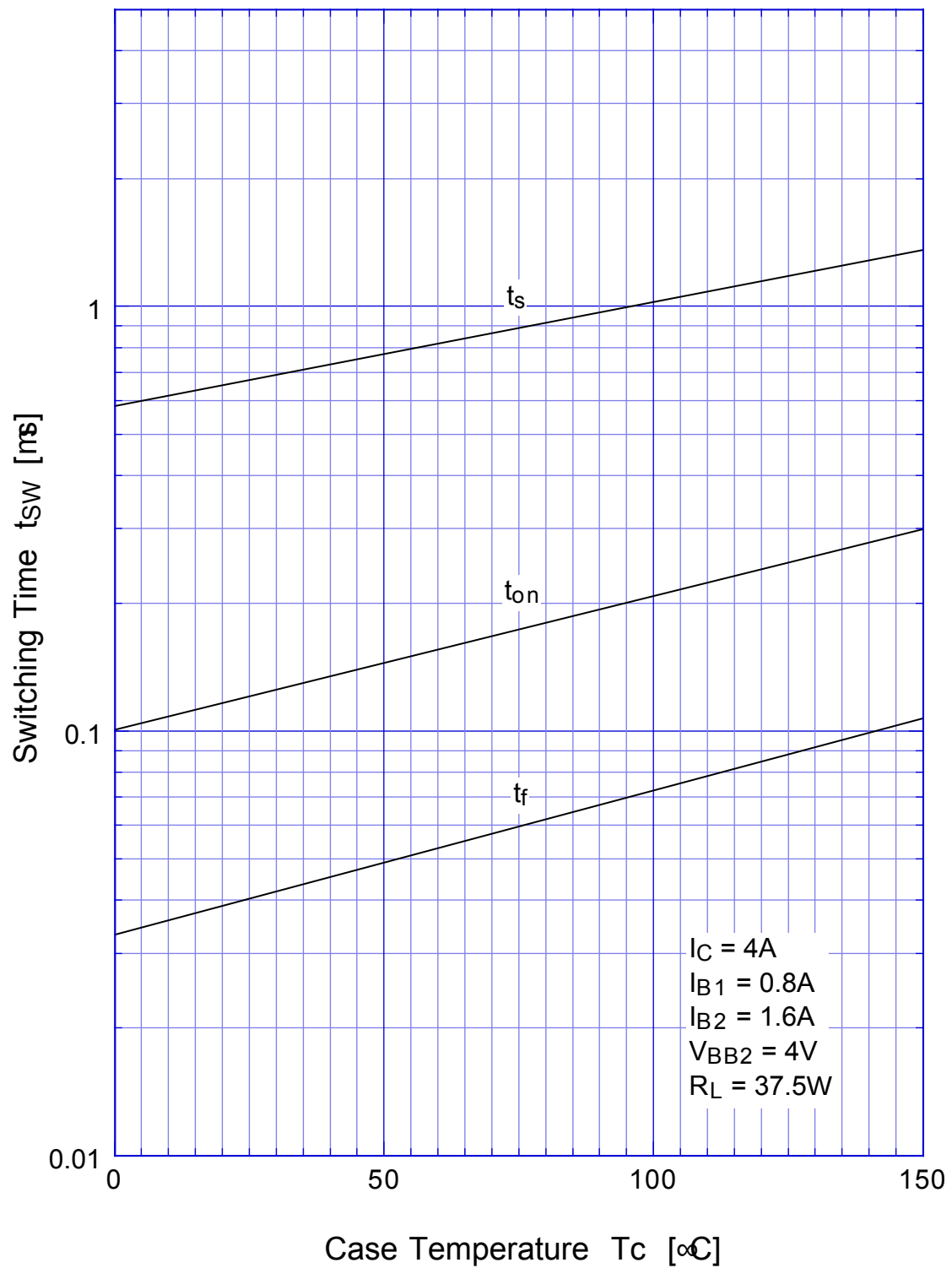
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Switching Time - I_C



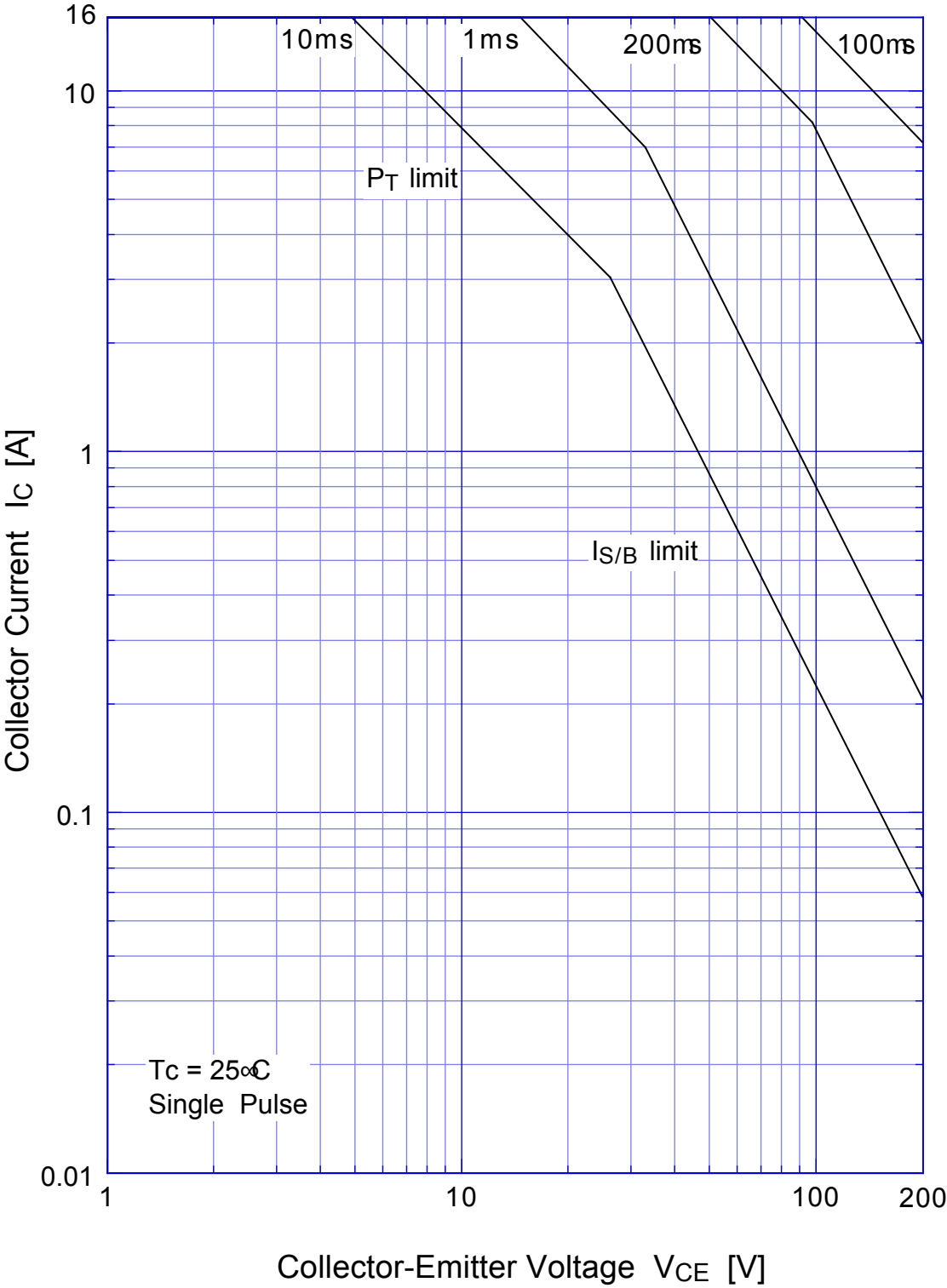
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Switching Time - T_c

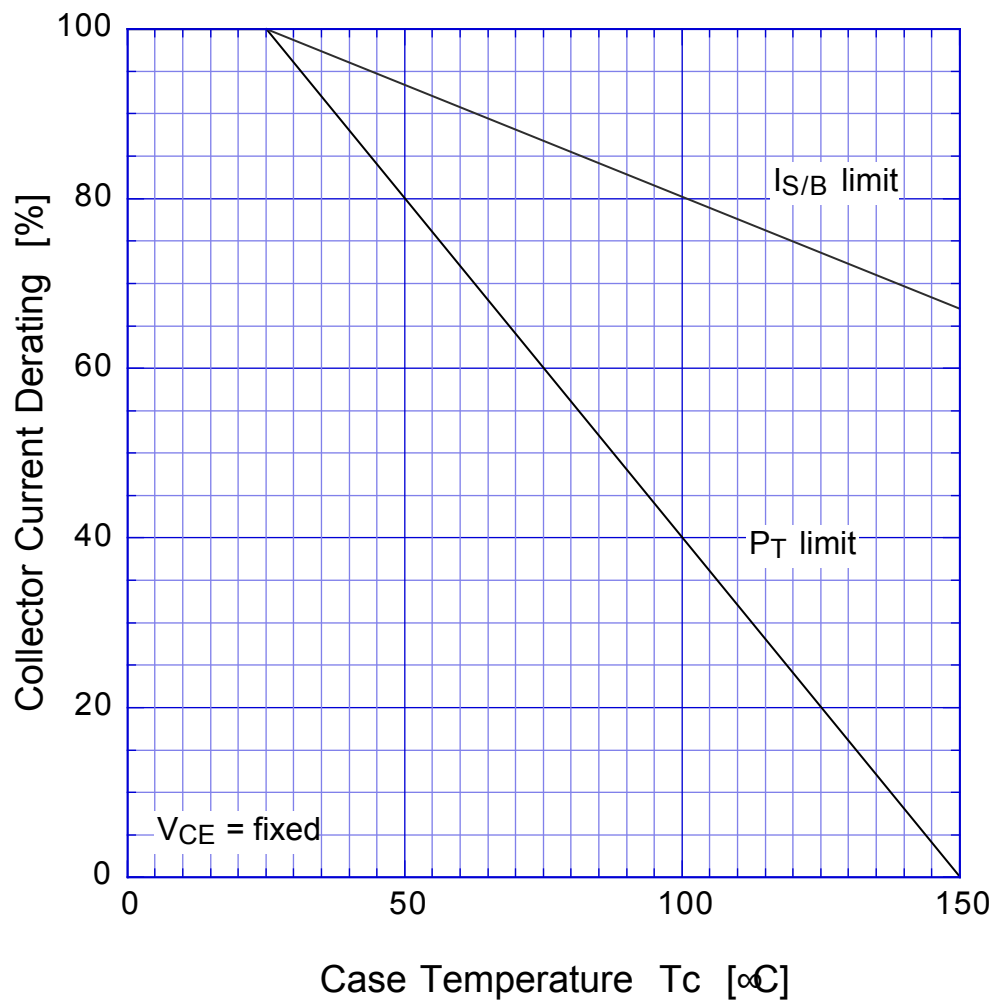


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Forward Bias SOA

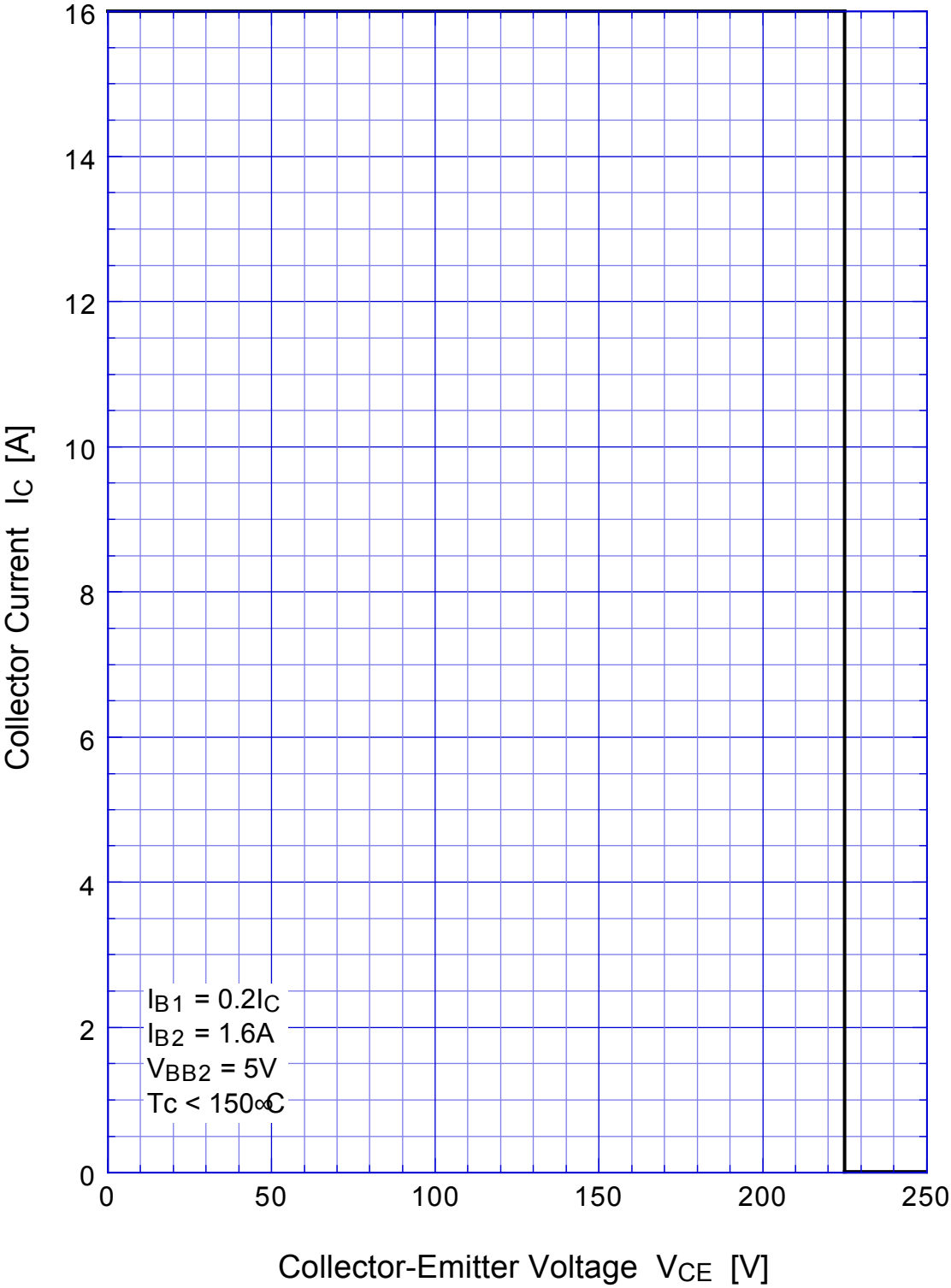


2SC4664 Collector Current Derating



2SC4664

Reverse Bias SOA



2SC4664 Transient Thermal Impedance

